



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

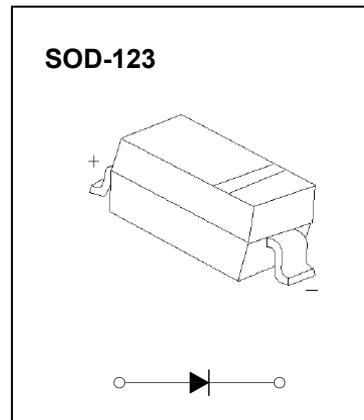
SOD-123 Plastic-Encapsulate Diodes

B0520L W/B0530W/B0540W

SCHOTTKY BARRIER DIODE

FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- High Conductance
- Also Available in Lead Free Version

MARKING: B0520LW:SD**B0530W: SE****B0540W: SF**

Maximum Ratings @Ta=25°C

Parameter	Symbol	B0520LW	B0530W	B0540W	Unit
Peak Repetitive Peak Reverse Voltage	V _{RRM}				
Working Peak Reverse Voltage	V _{RWM}	20	30	40	V
DC Blocking Voltage	V _R				
RMS Reverse Voltage Reverse Voltage (DC)	V _{R(RMS)}	14	21	28	V
Average Rectified Output Current	I _o		0.5		A
Forward Current Surge Peak	I _{FSM}		5.5		A
Power Dissipation	P _D		500mW		AmW
Thermal Resistance Junction to Ambient	R _{θJA}		0.08°C/W		°C/W
Junction Temperature	T _j		125		°C
Storage Temperature	T _{STG}		-55~+150		°C
Voltage Rate of Change	dv/dt		1000		V/μs

Electrical Characteristics @Ta=25°C

Parameter	Symbol	B0520LW	B0530W	B0540W	Unit	Test Conditions
Minimum reverse breakdown voltage	V _(BR)	20	--	--	V	I _R =250μA
		--	30	--		I _R =200μA
		--	--	40		I _R =20μA
Forward voltage	V _{F1}	0.32	0.375	--	V	I _F =0.1A
	V _{F2}	0.385	0.430	0.510		I _F =0.5A
	V _{F3}	--	--	0.62		I _F =1A
Reverse current	I _{R1}	75	--	--	μA	V _R =10V
	I _{R2}	--	20	--		V _R =15V
Reverse current	I _{R3}	250	--	10	μA	V _R =20V
	I _{R4}	--	130	--		V _R =30V
	I _{R5}	--	--	20		V _R =40V
Capacitance between terminals	C _T	--	--	170	pF	V _R =0,f=1MHz

Typical Characteristics

B0530W

